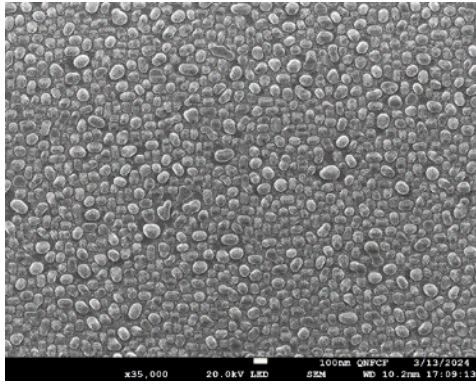
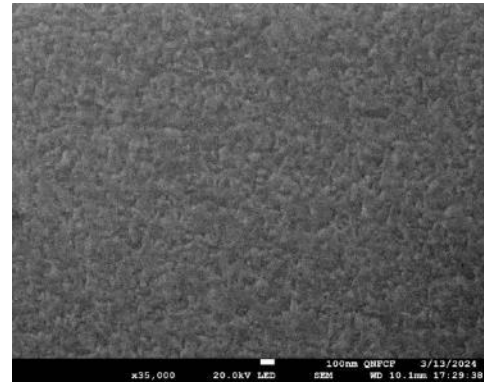


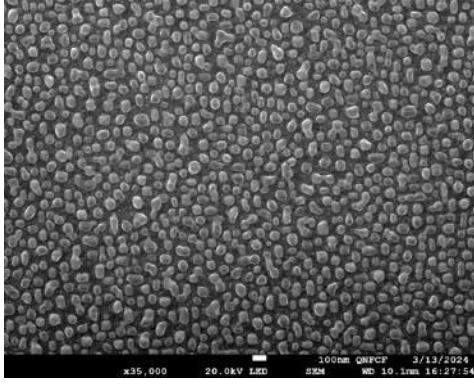
a) S-1



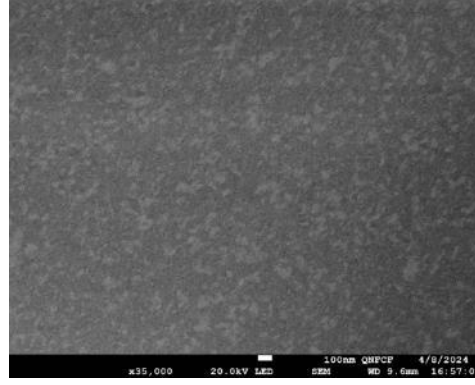
b) S-2



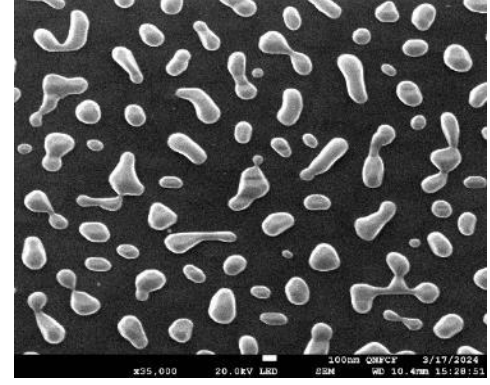
c) S-3



d) S-4



e) S-5



Sample	Underlying layer	Al growth rate ($\text{\AA}/\text{s}$)
S-1	$\text{In}_{0.75}\text{Ga}_{0.25}\text{As}$	0.1
S-2	$\text{In}_{0.75}\text{Ga}_{0.25}\text{As}$	3
S-3	InSb	0.1
S-4	InSb (Sb-rich)	3
S-5	InSb (Sb-depleted reconstruction)	3

The five figures illustrate the SEM scans of the surface morphology of five different samples, all examined at the same magnification and using the same driving voltage of 20 KV, although the resolution may differ between pictures. The differences between the samples are detailed in the table provided above.

As mentioned in the abstract, the Al surface exhibits discontinuous Aluminum (Al) islands when Al is grown at a low rate of $0.1 \text{ \AA}/\text{s}$ on $\text{In}_{0.75}\text{Ga}_{0.25}\text{As}$ and InSb (samples S-1 and S-3). Conversely, at the higher growth rate of $3 \text{ \AA}/\text{s}$, the Al layers are continuous on the $\text{In}_{0.75}\text{Ga}_{0.25}\text{As}$ surface layer (sample S-2) and on the InSb layer with an Sb-rich surface (sample S-4). However, for the growth of Al at $3 \text{ \AA}/\text{s}$ on the InSb layer with an Sb-depleted reconstruction in sample S-5, Al was observed to dewet on the surface, as demonstrated in Figure (d).